



### 40V 175°C P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C		
-40V	$29m\Omega$ @ $V_{GS} = -10V$	-8.0A		
<del>-4</del> 0V	45mΩ @ V <sub>GS</sub> = $-4.5$ V	-6.0A		

### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

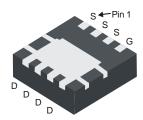
### **Features and Benefits**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- Low R<sub>DS(ON)</sub> Ensures On State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMPH4029LFGQ)

### **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)

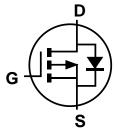




**Bottom View** 



Top View



**Equivalent Circuit** 

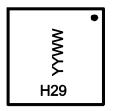
#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMPH4029LFG-7	PowerDI3333-8	2000/Tape & Reel
DMPH4029LFG-13	PowerDI3333-8	3000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**



H29= Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of year (ex: 19 = 2019) WW = Week Code (01 to 53)



### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	$V_{DSS}$	-40	V		
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Dusin Compart (Nata C) V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-8.0 -6.7	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	$T_C$ = +25°C $T_C$ = +70°C	I <sub>D</sub>	-22 -18	А
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%	I <sub>DM</sub>	-88	Α		
Maximum Continuous Body Diode Forward Current (	Is	-2.0	Α		
Pulsed Source Current (380μs Pulse, Duty Cycle = 1	I <sub>SM</sub>	-88	Α		
Avalanche Current (Note 7) L = 0.1mH	I <sub>AS</sub>	-25	А		
Avalanche Energy (Note 7) L = 0.1mH	E <sub>AS</sub>	32	mJ		

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P <sub>D</sub>	1.2	W
The small Besistance (hundring to Ambient (Nets 5)		1	125	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	85	C/VV
Total Power Dissipation (Note 6)		$P_{D}$	2.8	W
Thermal Resistance, Junction to Ambient (Note 6)  Steady st t<10s		$R_{ hetaJA}$	54	°C/W
			36	
Thermal Resistance, Junction to Case (Note 6)	$R_{ heta JC}$	6		
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +175	°C

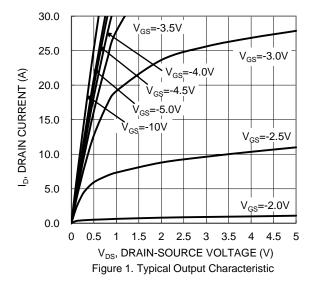
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	$BV_{DSS}$	-40			V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C				-1	μΑ	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage		1	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	1	-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance		_	18	29	mΩ	$V_{GS} = -10V, I_D = -3A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		23	45		$V_{GS} = -4.5V, I_{D} = -3A$	
Diode Forward Voltage	$V_{SD}$	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	_	1626		рF	.,	
Output Capacitance	Coss	-	135	1	рF	$V_{DS} = -20V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss		107	_	pF	1 = 1.0MHZ	
Gate Resistance	$R_g$		11	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	_	17	1	nC		
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	_	34	_	nC	$V_{DS} = -20V, I_{D} = -3A$	
Gate-Source Charge	$Q_{gs}$	-	3.7	_	nC	$V_{DS} = -20V$ , $I_D = -3A$	
Gate-Drain Charge	$Q_{gd}$	_	6.0	_	nC	1	
Turn-On Delay Time	t <sub>D(ON)</sub>	1	3.9	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	2.8	_	ns	$V_{GS} = -10V, V_{DS} = -20V,$ $R_G = 3\Omega, I_D = -3A$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	83	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	30	_	ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	17.3	_	ns	I <sub>F</sub> = -3A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge		_	7.2	_	nC	I <sub>F</sub> = -3A, di/dt = 100A/μs	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.





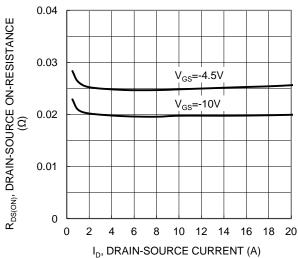


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

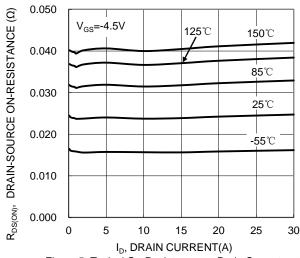


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

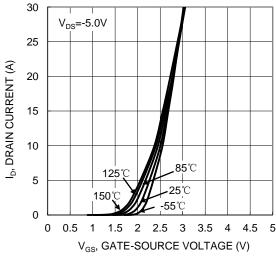
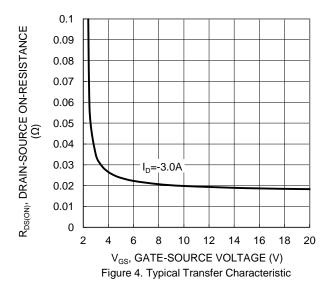


Figure 2. Typical Transfer Characteristic



2.5 R<sub>DS(ON)</sub>, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) 2  $V_{GS} = -10V, I_{D} = -10A$ 1.5  $V_{GS}$ =-4.5V,  $I_{D}$ =-5A 1 0.5 0 -25 -50 0 25 50 75 100 125 150 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Figure 6. On-Resistance Variation with Temperature



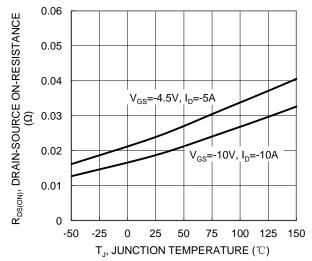
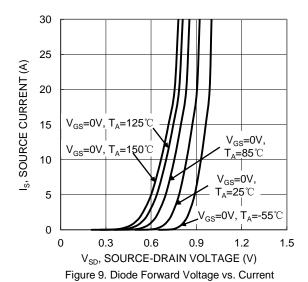
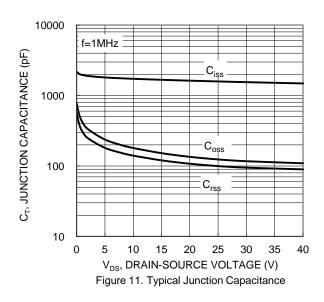


Figure 7. On-Resistance Variation with Temperature





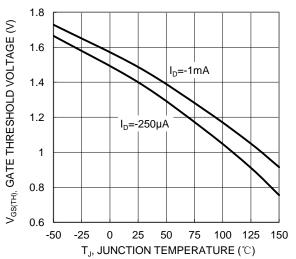


Figure 8. Gate Threshold Variation vs. Junction Temperature

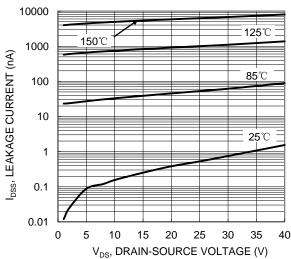


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

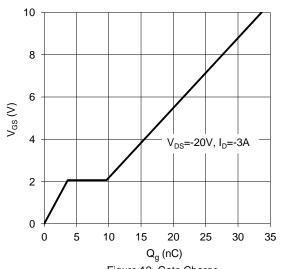
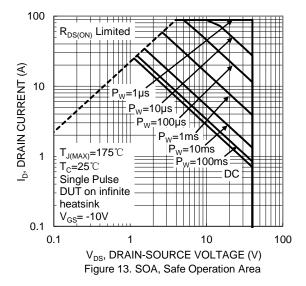


Figure 12. Gate Charge





r(t), TRANSIENT THERMAL RESISTANCE D=0.5 D=0.9 D=0.3 D=0.7 0.1 D=0.1 D=0.05 D=0.02 0.01 D=0.005  $\begin{array}{l} R_{\theta JA}(t) {=} r(t) \ ^*R_{\theta JA} \\ R_{\theta JA} {=} 125\, ^{\circ} \text{C/W} \\ \text{Duty Cycle, D=t1 / t2} \end{array}$ D=Single Pulse 0.001 0.0001 0.001 0.01 0.1 1 10 100 1000 t1, PULSE DURATION TIME (sec)

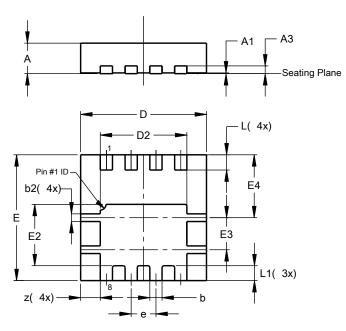
Figure 14. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8

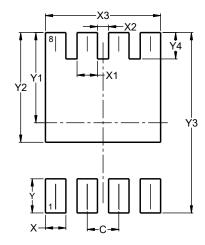


PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	-	-	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	_	_	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	_	0.515		
All Dimensions in mm					

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8



Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Y	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		
Y4	0.540		



#### IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### **LIFE SUPPORT**

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2019, Diodes Incorporated

www.diodes.com